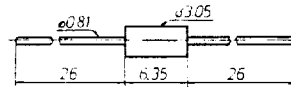
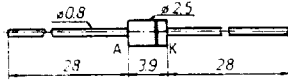
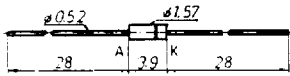


SILICON DIODES

SMALL SIGNAL, REFERENCES, MICROWAVE



CASES: DO-35

DO-41

F-126 (White band near cathode)

HIGH SPEED SWITCHING DIODES

Case DO-35

TYPE	V _R min. (V)	I _F max. (mA)	V _F / I _F max. (V)/(mA)	I _{FSM} (A)	C _{tot} max. (pF)	t _{rr} max. (ns)
1N 4148	75	200	1 / 10	2	4	4
1N 4149	75	200	1 / 10	2	4	4
1N 4151	50	200	1 / 50	2	2	2
1N 4154	25	200	1 / 30	2	4	4
1N 4446	75	200	1 / 20	2	4	4
1N 4447	75	200	1 / 20	2	2	4
1N 4448	75	200	1 / 100	2	4	4
1N 4449	75	200	1 / 30	2	2	4
1N 4454	50	200	1 / 10	2	2	2
BAY 93	20	150	1 / 10	2	4	15

AVALANCHE DIODES FOR TELEPHONY

Case DO-35

BAW 21	70	400	1 / 200	6	35	50
BAX 12	90	400	1 / 200	6	35	50

BAND SWITCHING DIODES

Case DO-35

TYPE	V _R min. (V)	I _F max. (mA)	V _F / I _F max. (V)/(mA)	r _f max. (ohms)	C _{tot} @ V _R max. (pF)	V _R (V)
BA 243	20	100	1 / 100	1	2	15
BA 244	20	100	1 / 100	0.7	2	15

ULTRA-LOW LEAKAGE DIODES

Case DO-35

TYPE	V _R min. (V)	I _F max. (mA)	V _F / I _F max. (V)/(mA)	I _R max. (pA)	V _R (V)	C _{tot} max. (pF)
DP 450	20	50	1 / 10	5	5.0	1.5
DP 451	20	50	1 / 10	10	5.0	1.5

VARIABLE CAPACITANCE DIODES

Case DO-35

TYPE	V _R min. (V)	C _{tot} @ f=1MHz min.-max. (pF)	V _R (V)	C _{tot} RATIO min.-max.	V _s max. (V/V)	r _s max. (ohms)
BB 125	30	2 -3.2	25	4 - 6	3/25	0.8
BB 125A	30	2 -2.35	25	4 - 6	3/25	0.8
BB 125B	30	2.25-2.85	25	4 - 6	3/25	0.8
BB 125C	30	2.5-3.2	25	4 - 6	3/25	0.8
BB 126	30	2 - 3	25	4 - 6	3/25	1.2
BB 139	30	26 - 32	3	5 -6.5	3/25	0.5
B 310	12	16 - 28	4	1.6-2.25	4 / 9	
B 410	12	7.5-11.5	4	1.6-	4 / 9	

400 mW SILICON SCHOTTKY BARRIER DIODES

CASE DO-35

TYPE	PIV (V)	V _F max (V)	I _F @ V _F max (mA)	V _F @ I _F max (V)	I _R @ V _R max (uA)	C @ 1MHz (pF)	
SD101A	60	0.41	1	1.00	15	0.2 50	2.0
SD101B	50	0.40	1	0.95	15	0.2 40	2.1
SD101C	40	0.39	1	0.90	15	0.2 30	2.2
§ SD103A	40	0.37	20	0.60	200	5.0 30	50.0
§ SD103B	30	0.37	20	0.60	200	5.0 20	50.0
§ SD103C	20	0.37	20	0.60	200	5.0 10	50.0
§ SD104A	10	0.45	1	0.60	10	0.3 1	1.0
§ SD104B	5	0.45	1	0.60	10	0.3 1	1.0
§ SD104C	10	0.45	1	0.60	10	0.3 1	1.2
§ SD104D	5	0.45	1	0.60	10	0.3 1	1.2
§ SD104E	10	0.425	1	0.55	10	0.3 1	1.5
§ SD104F	5	0.425	1	0.55	10	0.3 1	1.5

§ Preliminary data

GENERAL APPLICATION DIODES

Case DO-35

TYPE	V _R min. (V)	I _F max. (mA)	V _F / I _F max. (V)/(mA)	I _R max. (nA)	r _f max. (ohms)	t _{rr} max. (ns)
BA 170	20	150	1 / 80	100	0.5	100
BA 171	30	150	1 / 80	100	0.5	100
BA 172	50	150	1 / 80	100	0.5	100

TEMPERATURE COMPENSATED REFERENCES

Case DO-35

TYPE	V _Z typ. (V)	r _{ZT} max. (ohms)	TEST TEMP. (°C)	V _Z max. (mV)	MAX TEMP. COEFF. (x10 ⁻⁴ /°C)
BZV 43	6.2	20	0/25/100	62	1
BZV 44	6.2	20	0/25/100	31	0.5
BZV 45	6.2	20	0/25/100	12	0.2
ZTC 33	33	25			-1 / +0.5

THERMOCONTROLLED VOLTAGE REGULATORS

Cases F-126 / DO-41

TYPE	V _Z typ. (V)	V _Z min.-max. (V)	I _{ZT} (mA)	r _{ZT} max. (ohms)	VOLTAGE DRIFT (mV/°C)
DL 5V6A	5.6	5.3-5.9	7.5	75	2.5-4
DL 5V6B	5.6	5.3-5.9	7.5	75	3.4-5.5
DL 6V2A	6.2	5.7-6.6	7.5	75	3-4.5
DL 6V2B	6.2	5.7-6.6	7.5	75	3.75-6
DL 6V8A	6.8	6.4-7.2	7.5	75	3.3-4.8
DL 6V8B	6.8	6.4-7.2	7.5	75	4.4-6.8

REFERENCE DIODES

Case F-126

TYPE	I _{FM} #1 (mA)	V _F min.-max. (V)	I _F (mA)	r _f max. (ohms)
DRD 1	250	0.40-0.50	0.1	680
		0.52-0.63	1	65
		0.66-0.66	2	34
		0.61-0.71	5	13
		0.65-0.74	10	6.7
		0.75-0.95	100	0.7
DRD 2	250	0.80-1.00	0.1	1300
		1.05-1.25	1	135
		1.11-1.33	2	68
		1.19-1.42	5	26
		1.25-1.50	10	13
		1.50-1.75	100	2
DRD 3	250	1.60-1.90	250	1.1
		1.22-1.42	0.1	2250
		1.62-1.83	1	205
		1.74-1.94	2	100
		1.87-2.08	5	42
		1.98-2.18	10	21
DRD 4	250	2.30-2.60	100	3.5
		2.50-2.80	250	2.5
		1.50-1.90	0.1	3100
		2.07-2.37	1	275
		2.23-2.50	2	180
		2.45-2.67	5	55
		2.60-2.80	10	27
		3.00-3.30	100	4.5
		3.20-3.50	250	3.5

* T_{VJ} = 25°C